

Electroluminescence enhancement in mid-infrared InAsSb resonant cavity light emitting diodes for CO₂ detection



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In this work, we demonstrated a mid-infrared resonant cavity light emitting diode (RCLED) operating near $4.2 \mu\text{m}$ at room temperature, grown lattice-matched on a GaSb substrate by molecular beam epitaxy, suitable for CO₂ gas detection. The device consists of a 1λ -thick microcavity containing an InAs_{0.90}Sb_{0.1} active region sandwiched between two high contrast, lattice-matched AlAs_{0.08}Sb_{0.92}/GaSb distributed Bragg reflector (DBR) mirrors. The electroluminescence emission spectra of the RCLED were recorded over the temperature range from 20 to 300 K and compared with a reference LED without DBR mirrors. The RCLED exhibits a strong emission enhancement due to resonant cavity effects. At room temperature, the peak emission and the integrated peak emission were found to be increased by a factor of ~ 70 and ~ 11 , respectively, while the total integrated emission enhancement was $\sim \times 33$. This is the highest resonant cavity enhancement ever reported